



## Description

The HXY3N10MI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = 100V$   $I_D = 3A$

$R_{DS(ON)} < 286m\Omega$  @  $V_{GS}=10V$

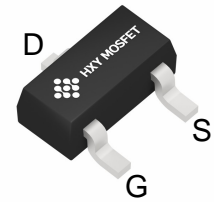
$R_{DS(ON)} < 312m\Omega$  @  $V_{GS}=4.5V$

## Application

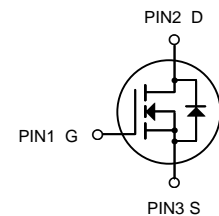
Battery protection

Load switch

Uninterruptible power supply



SOT-23-3L



N-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY3N10MI	SOT-23-3L	03N10	3000

## Absolute Maximum Ratings ( $T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	3	A
$I_{DM}$	Drain Current-Pulsed	1.4	A
$P_D$	Maximum Power Dissipation	2.3	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 175	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	$^{\circ}C/W$



**Electrical Characteristics ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =2A	-	220	286	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A	-	223	312	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V,I <sub>D</sub> =3A	-	5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V, F=1.0MHz	-	320	-	PF
Output Capacitance	C <sub>oss</sub>		-	20	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	14	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V, R <sub>L</sub> =19Ω V <sub>GS</sub> =10V,R <sub>G</sub> =3Ω	-	13	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	53	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	17	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =30V,I <sub>D</sub> =3A, V <sub>GS</sub> =10V	-	5.2	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.2	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =3A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	3	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$
4. Guaranteed by design, not subject to production



## Typical Electrical and Thermal Characteristics (Curves)

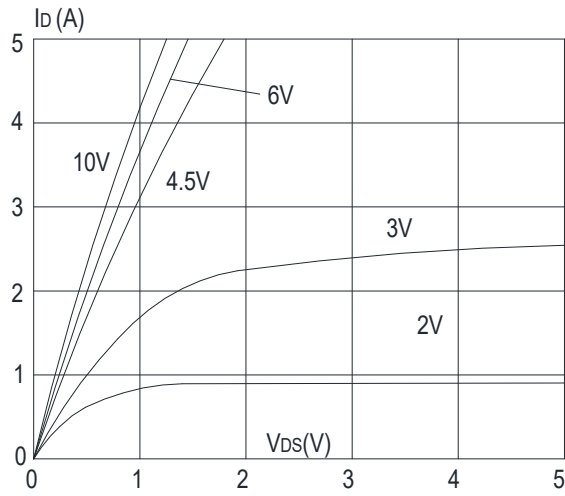


Figure1: Output Characteristics

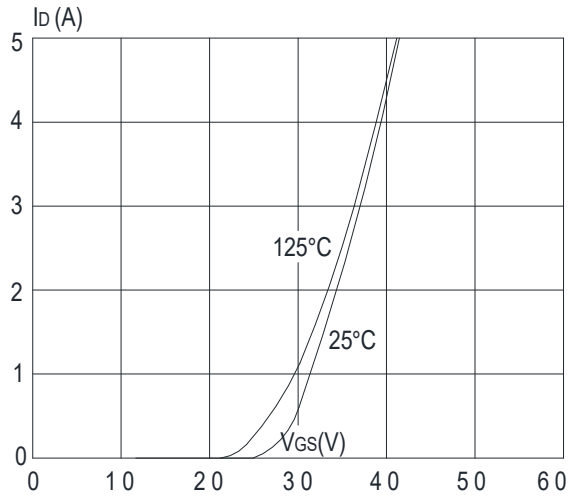


Figure 2: Typical Transfer Characteristics

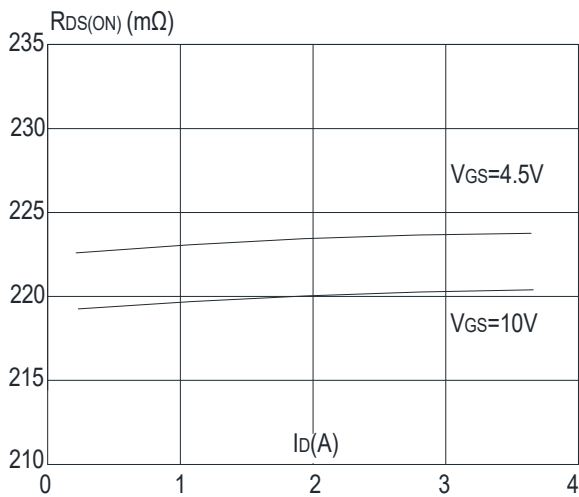


Figure 3: On-resistance vs. Drain Current

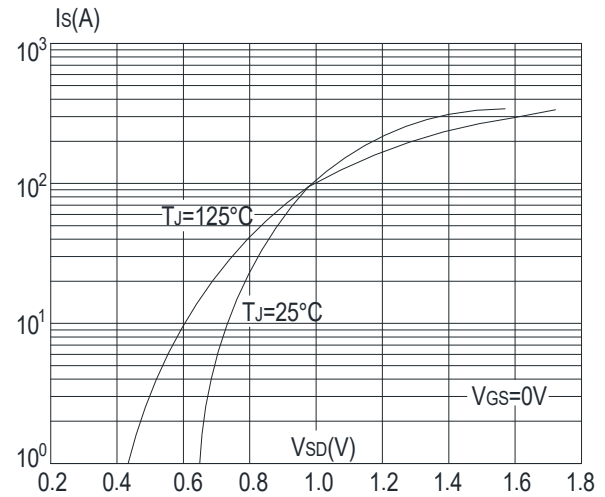


Figure 4: Body Diode Characteristics

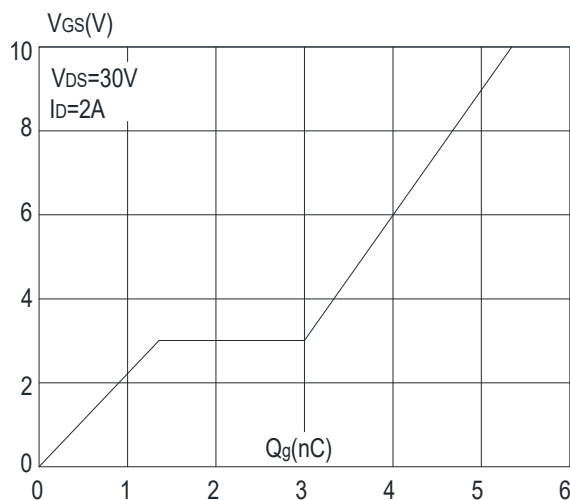


Figure 5: Gate Charge Characteristics

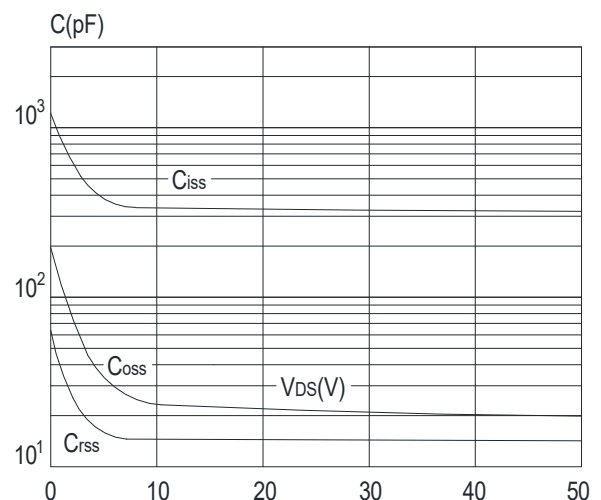
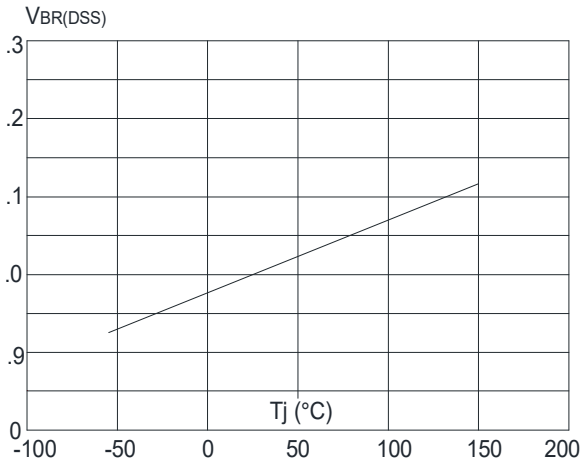
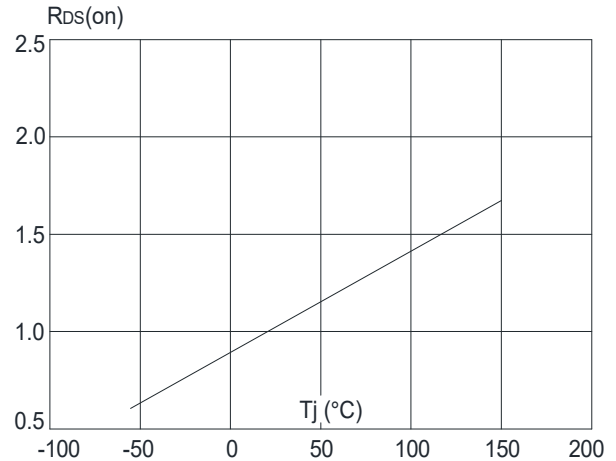


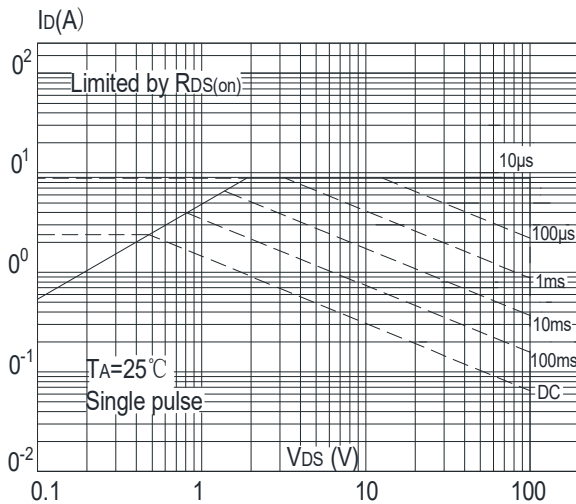
Figure 6: Capacitance Characteristics



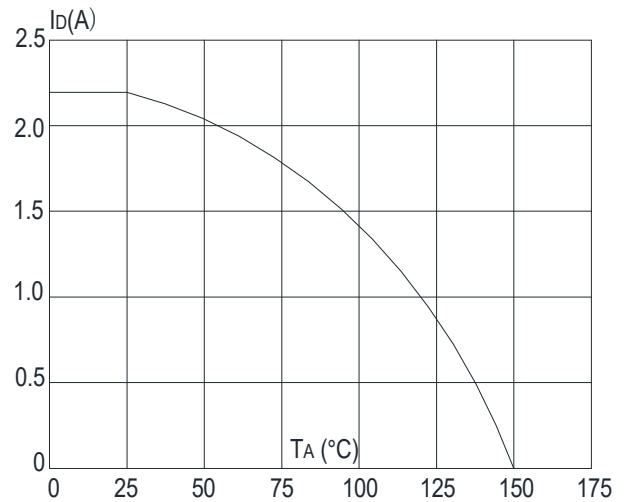
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



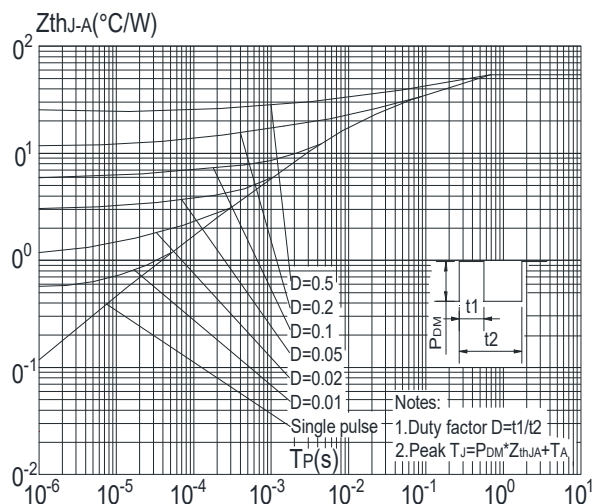
**Figure 8:** Normalized on Resistance vs. Junction Temperature



**Figure 9:** Maximum Safe Operating Area



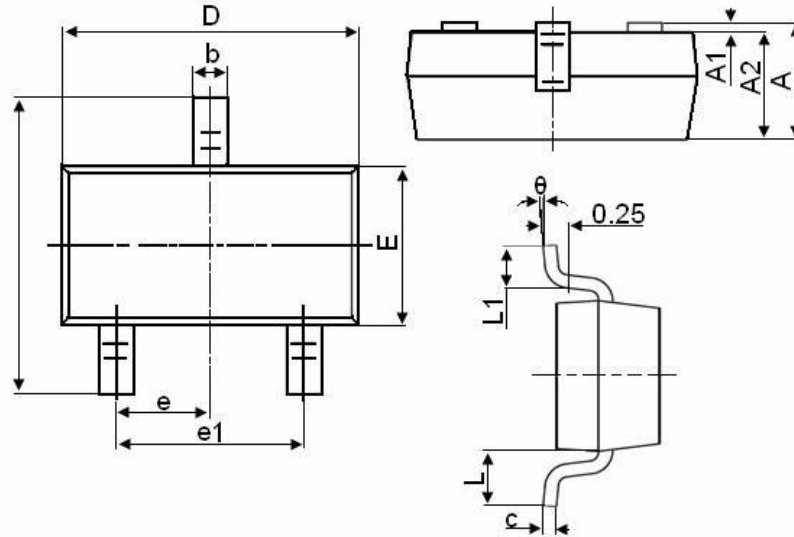
**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



## SOT-23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°



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